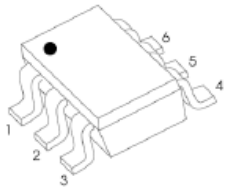
Plastic-Encapsulate Transistors

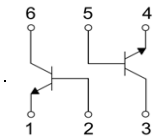
DUAL TRANSISTOR (NPN+NPN)

FEATURES

- Epitaxial planar die construction
- Ideal for low power amplification and switching

SOT-363





MARKING:K6N

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Power Dissipation	0.2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=30V,I_E=0			0.05	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.05	μA
Collector cut-off current	I_{CEX}	V_{CE}=30V,$V_{BE(off)}$=3V			0.05	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V,I_C=0.1mA	40			
	$h_{FE(2)}$	V_{CE}=1V,I_C=1mA	70			
	$h_{FE(3)}$	V_{CE}=1V,I_C=10mA	100		300	
	$h_{FE(4)}$	V_{CE}=1V,I_C=50mA	60			
	$h_{FE(5)}$	V_{CE}=1V,I_C=100mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	I_C=10mA,I_B=1mA			0.2	V
	$V_{CE(sat)2}$	I_C=50mA,I_B=5mA			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	I_C=10mA,I_B=1mA	0.65		0.85	V
	$V_{BE(sat)2}$	I_C=50mA,I_B=5mA			0.95	V
Transition frequency	f_T	V_{CE}=20V,I_C=10mA,f=100MHz	300			MHz
Collector output capacitance	C_{ob}	V_{CB}=5V,I_E=0,f=1MHz			4	pF
Noise figure	NF	V_{CE}=5V,I_c=0.1mA,f=1kHz,R_S=1KΩ			5	dB
Delay time	t_d	V_{CC}=3V, $V_{BE(off)}$=-0.5V I_C=10mA , I_{B1}=-I_{B2}= 1mA			35	nS
Rise time	t_r				35	nS
Storage time	t_s	V_{CC}=3V, I_C=10mA I_{B1}=-I_{B2}=1mA			200	nS
Fall time	t_f				50	nS

TYPICAL TRANSIENT CHARACTERISTICS

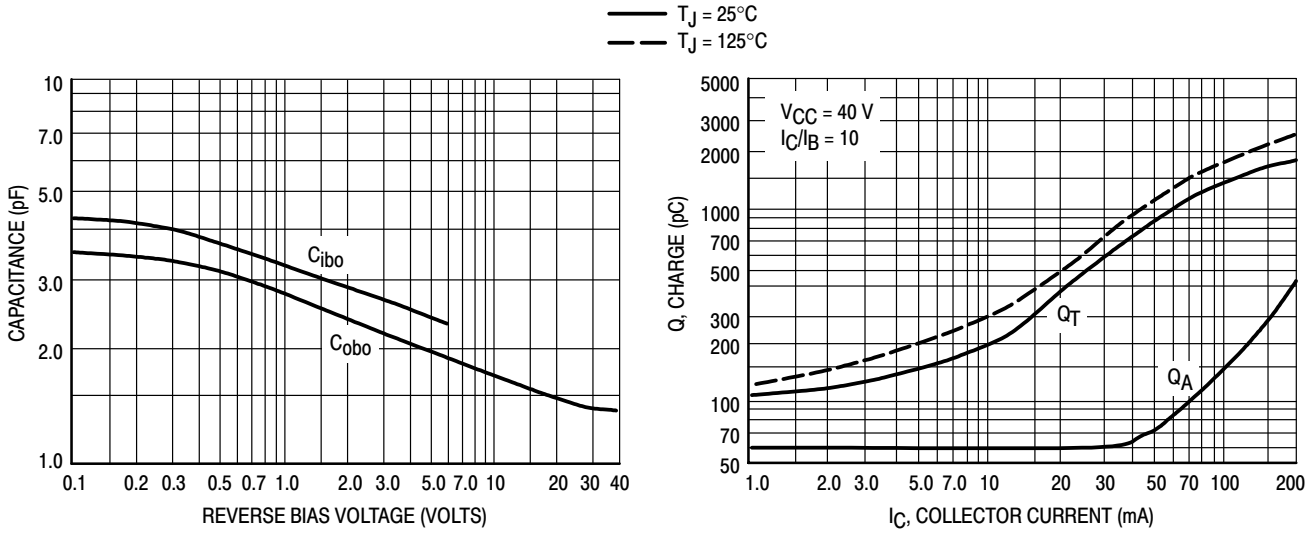


Figure 3. Capacitance

Figure 4. Charge Data

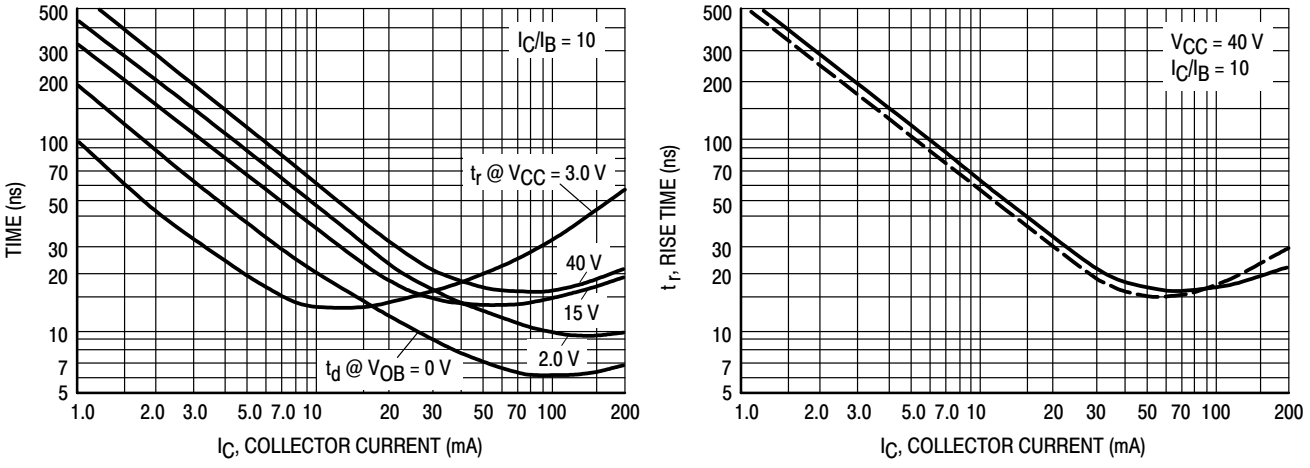


Figure 5. Turn–On Time

Figure 6. Rise Time

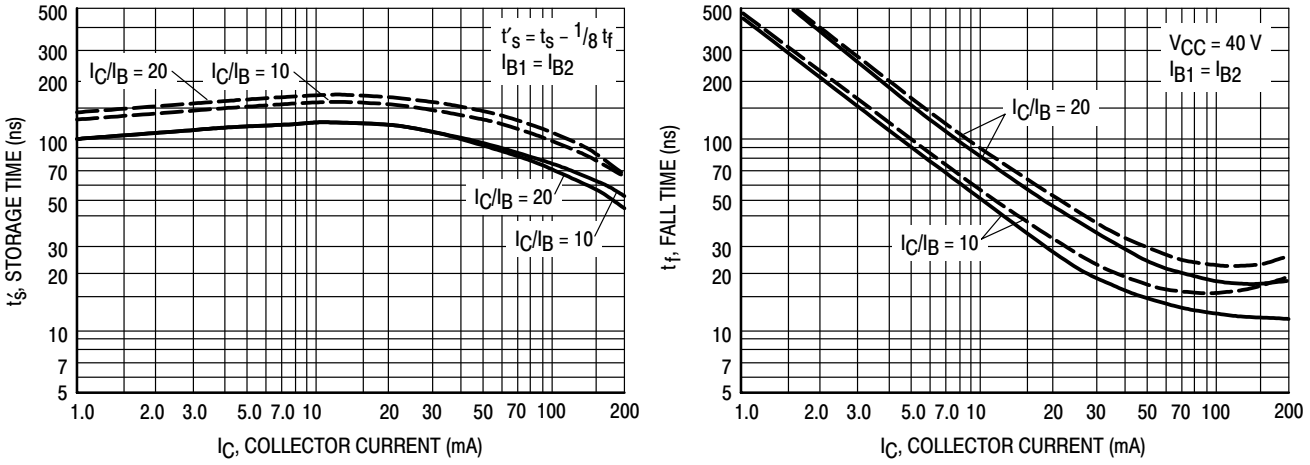


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL–SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = 5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

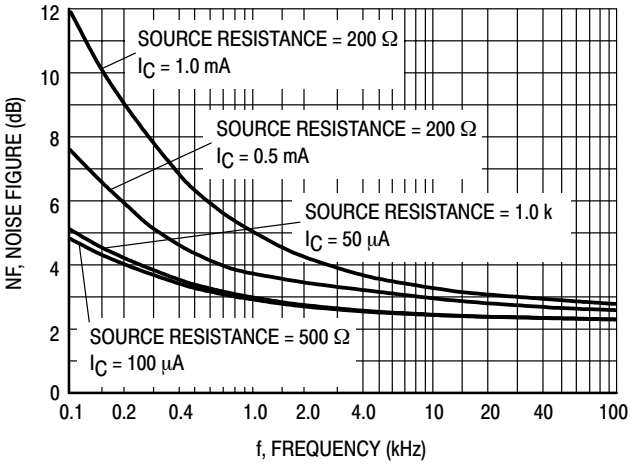


Figure 9. Noise Figure

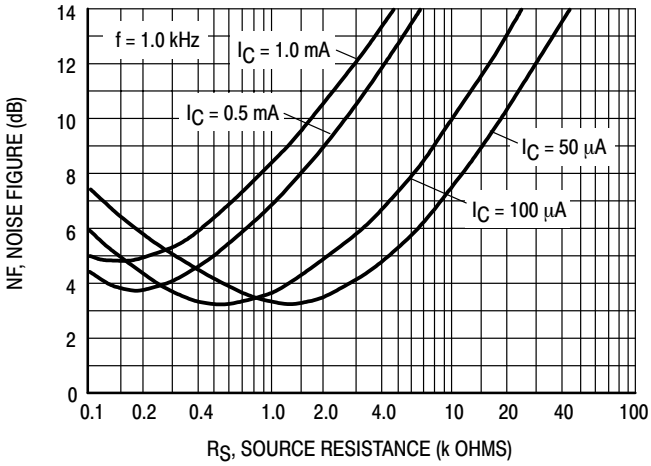


Figure 10. Noise Figure

h PARAMETERS

(V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C)

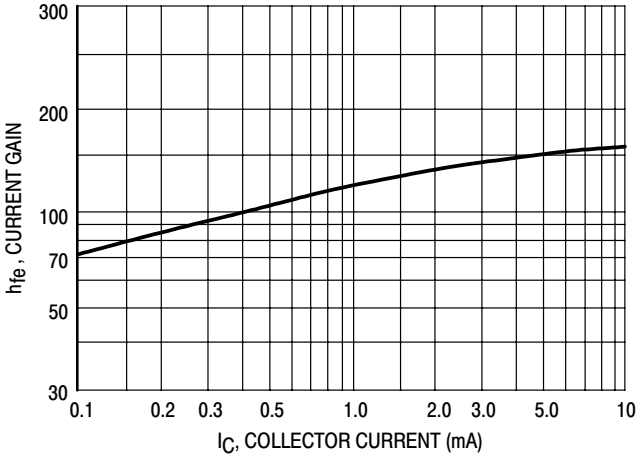


Figure 11. Current Gain

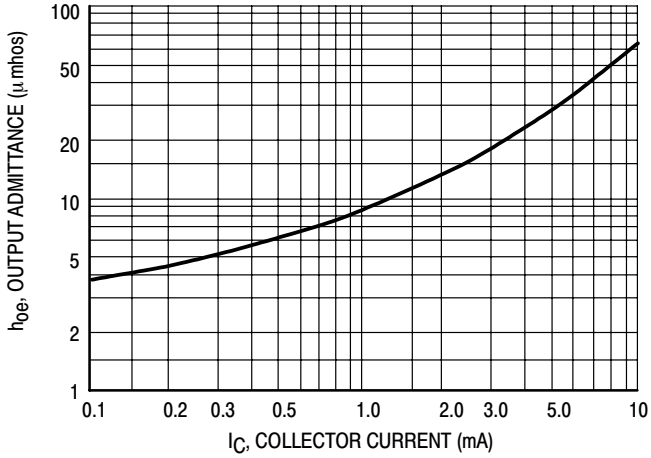


Figure 12. Output Admittance

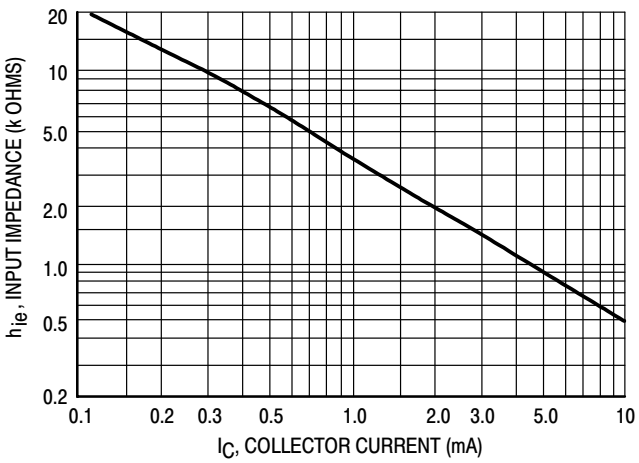


Figure 13. Input Impedance

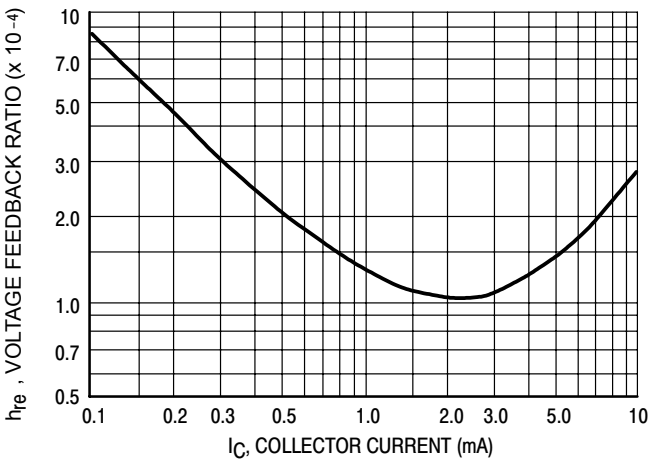


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

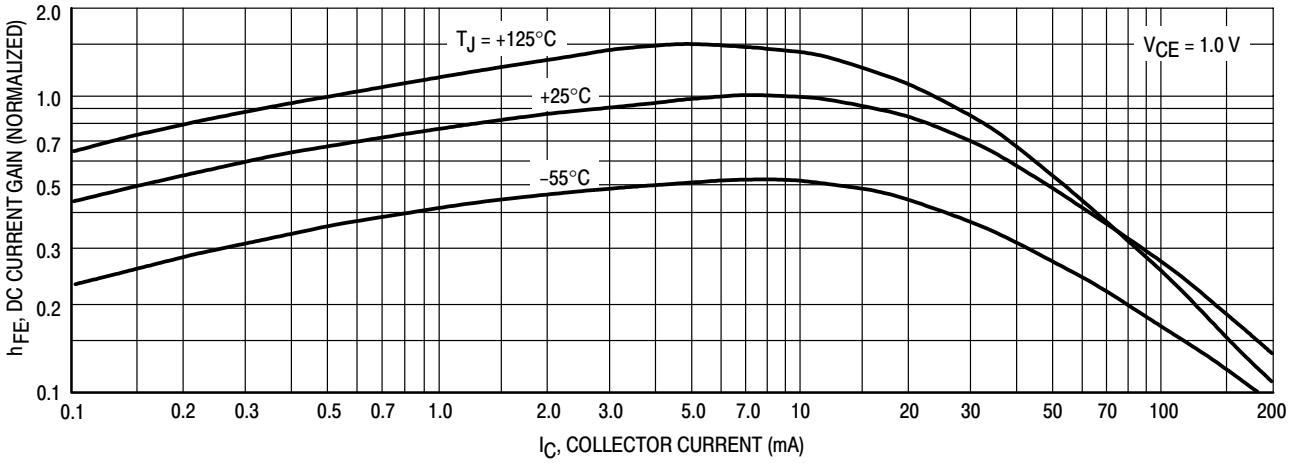


Figure 15. DC Current Gain

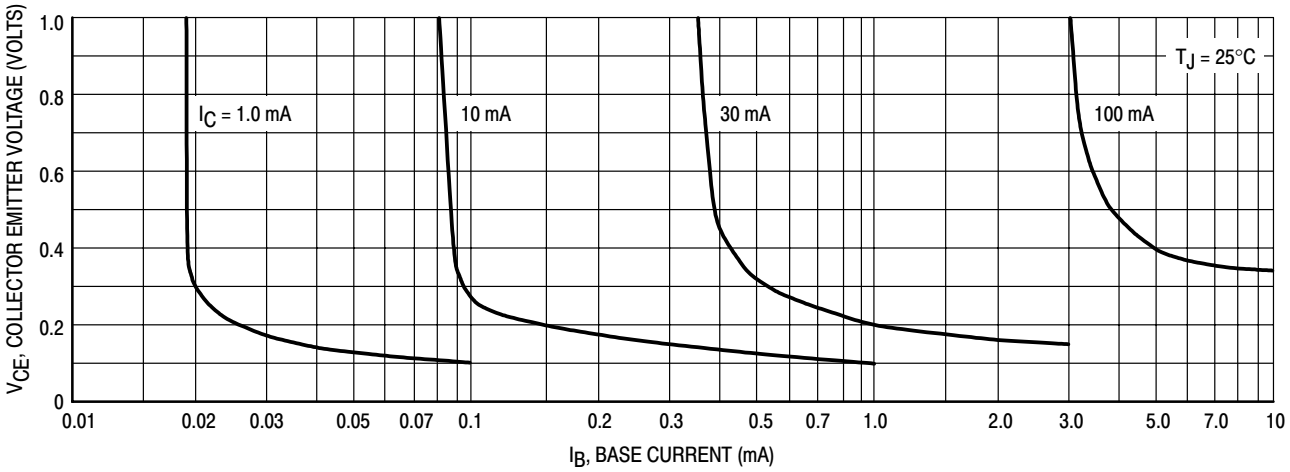


Figure 16. Collector Saturation Region

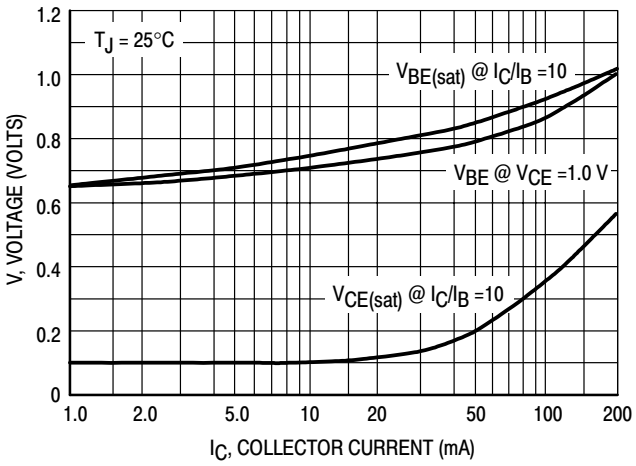


Figure 17. "ON" Voltages

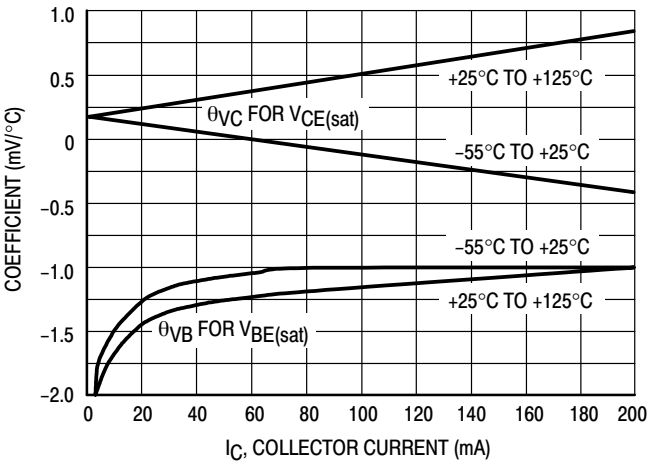
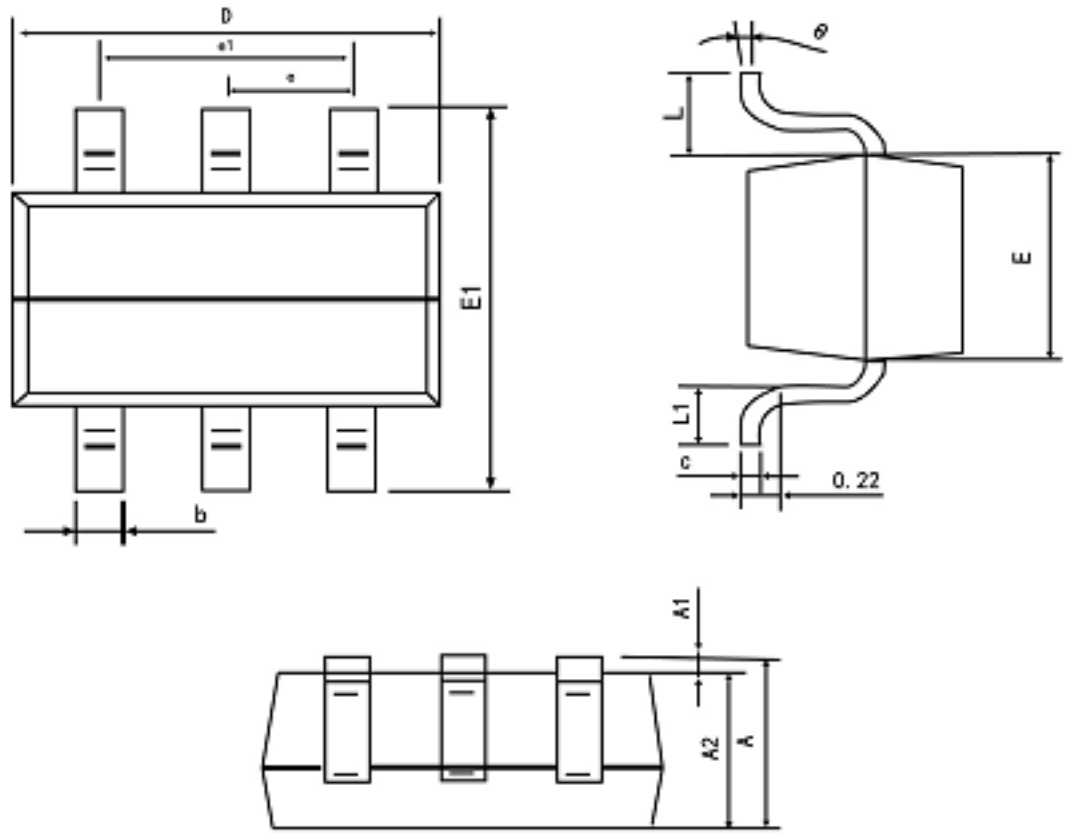


Figure 18. Temperature Coefficients

SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°